

A cross-sectional view of a substrate 201. A thin layer 202 is formed on the top surface of the substrate 201. A patterned layer 203 is formed on the top surface of the thin layer 202. The patterned layer 203 consists of a series of rectangular blocks.

A cross-sectional view of a semiconductor device. It shows a substrate 201 with diagonal hatching. On top of the substrate is a layer 203. A series of protrusions 204 are formed on the surface of layer 203.

FIG. 2B

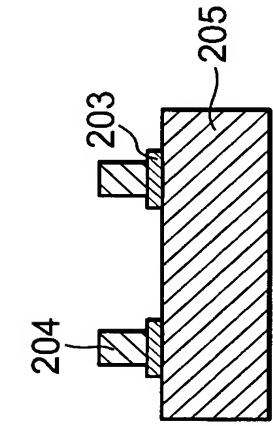


FIG. 2C

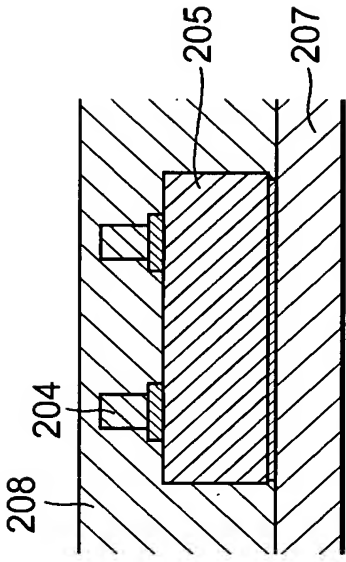


FIG. 2E

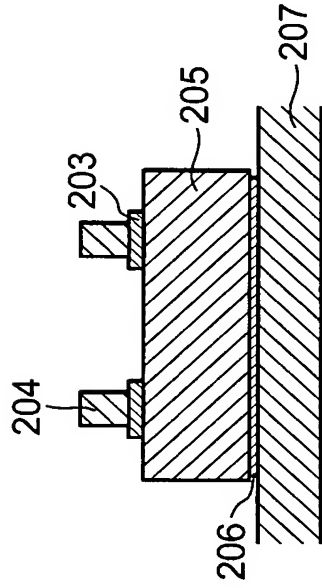


FIG. 2D

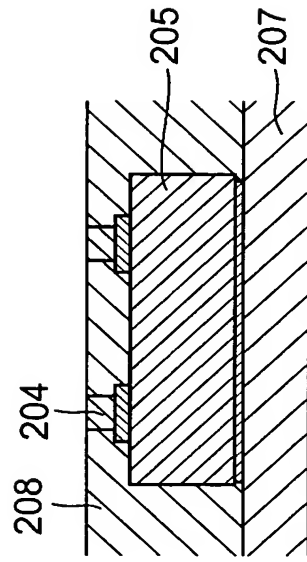


FIG. 2F

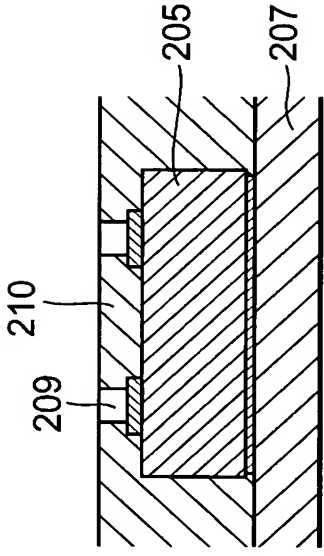


FIG. 2G

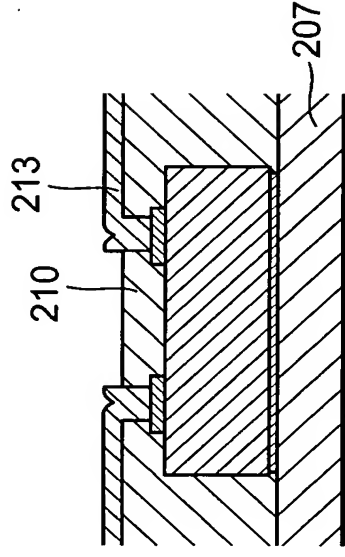


FIG. 2I

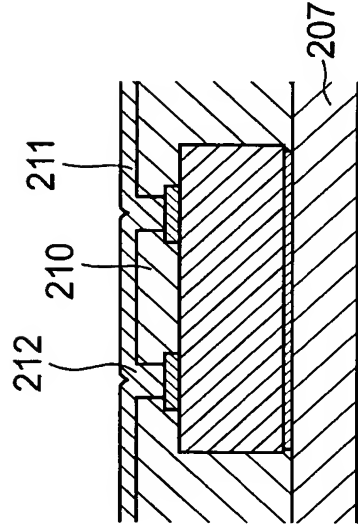


FIG. 2H

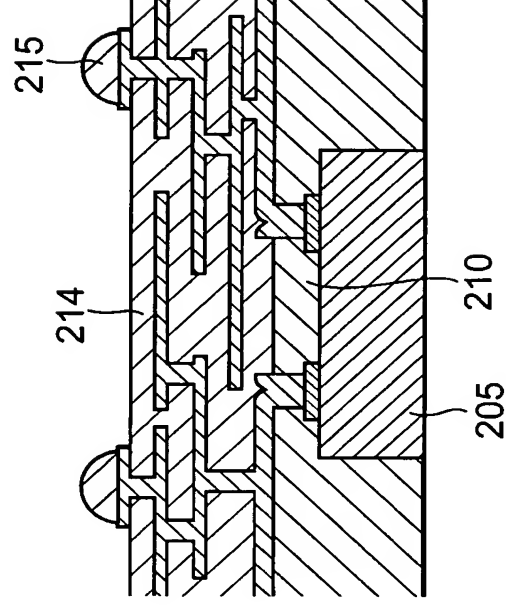


FIG. 2J

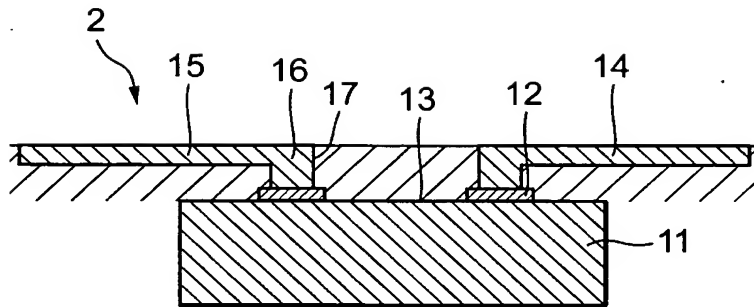


FIG. 3

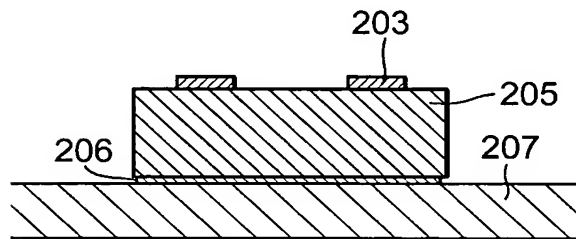


FIG. 4A

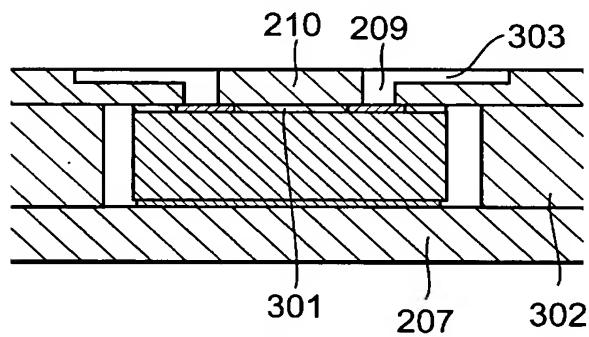


FIG. 4B

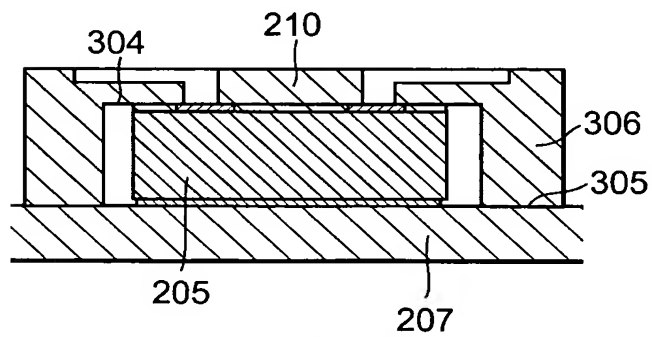


FIG. 4B-2

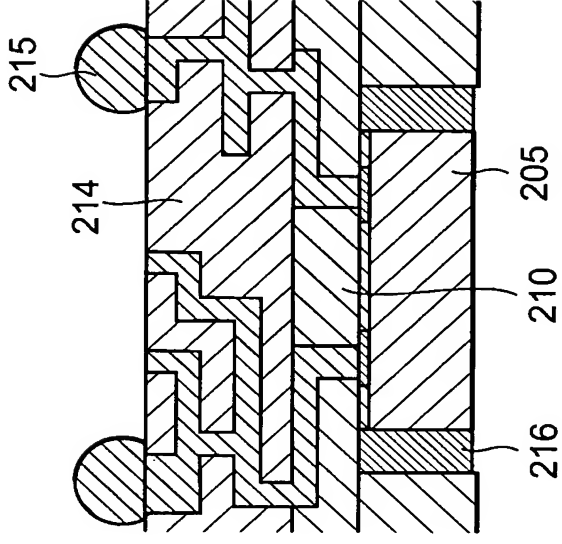


FIG. 4E

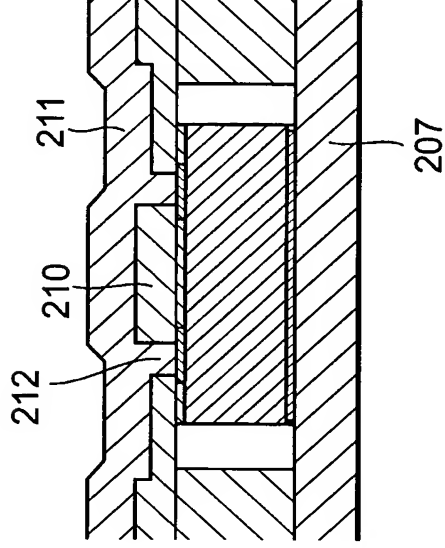


FIG. 4C

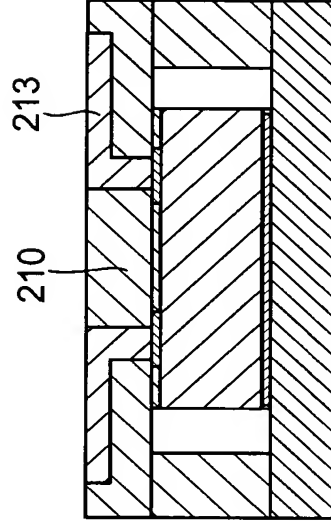
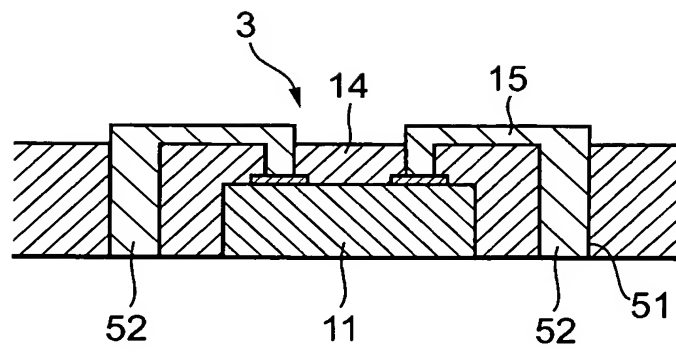
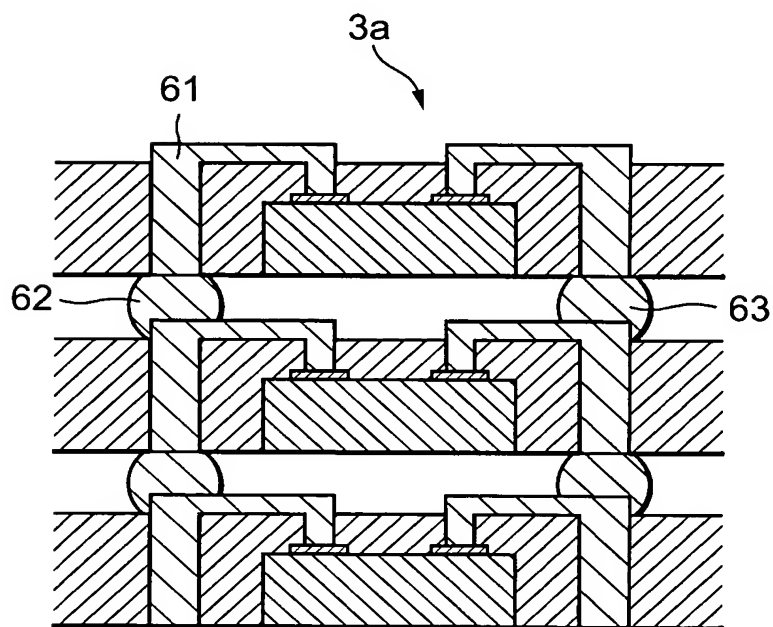


FIG. 4D

**FIG. 5****FIG. 6**

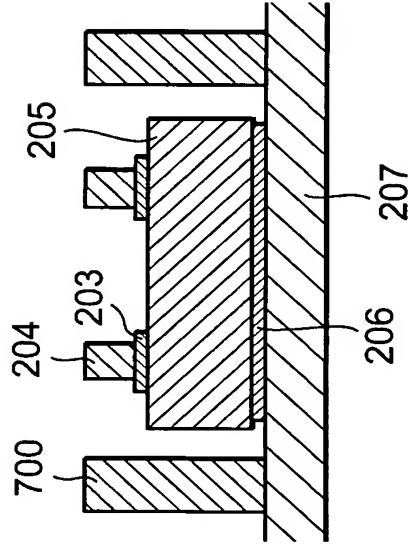


FIG. 7A

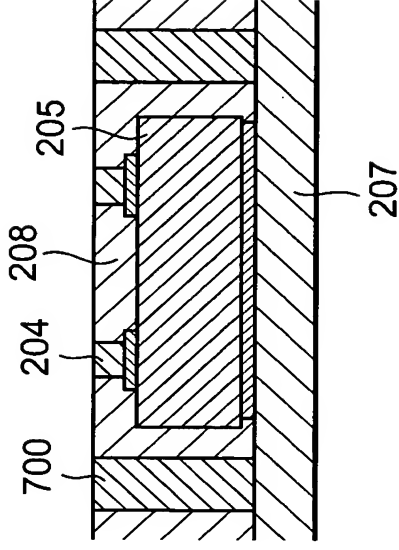


FIG. 7C

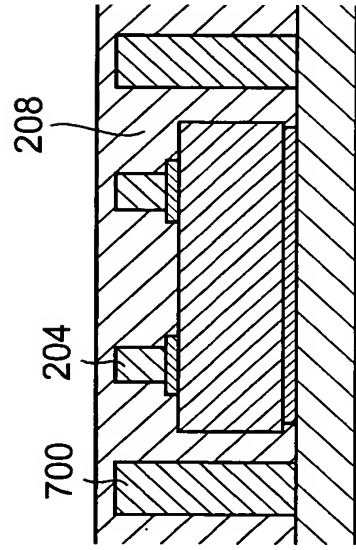


FIG. 7B

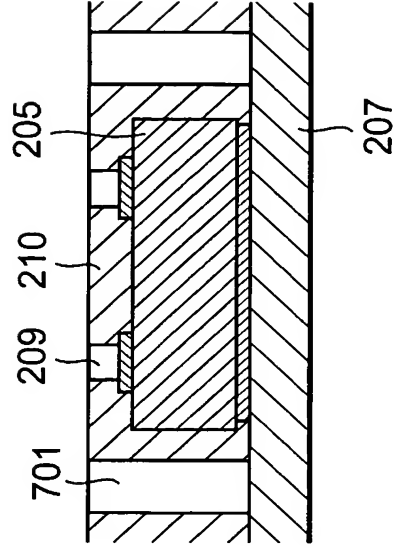


FIG. 7D

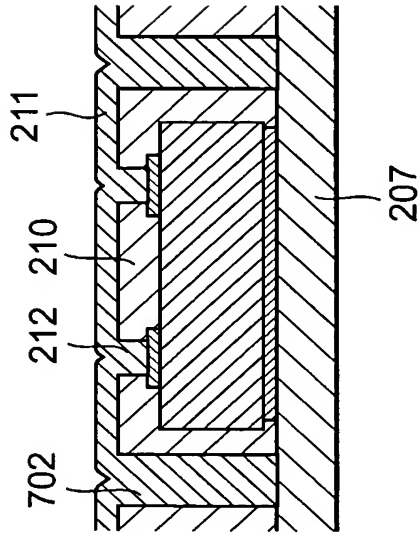


FIG. 7E

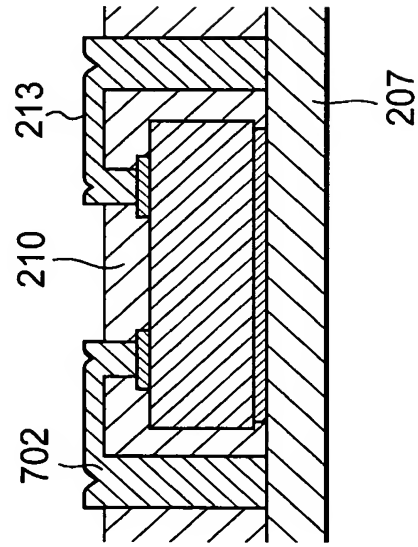


FIG. 7F

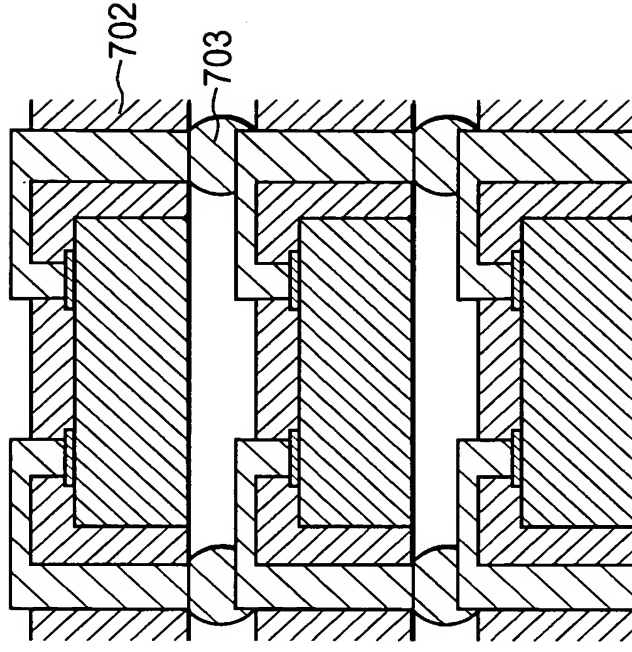


FIG. 7G

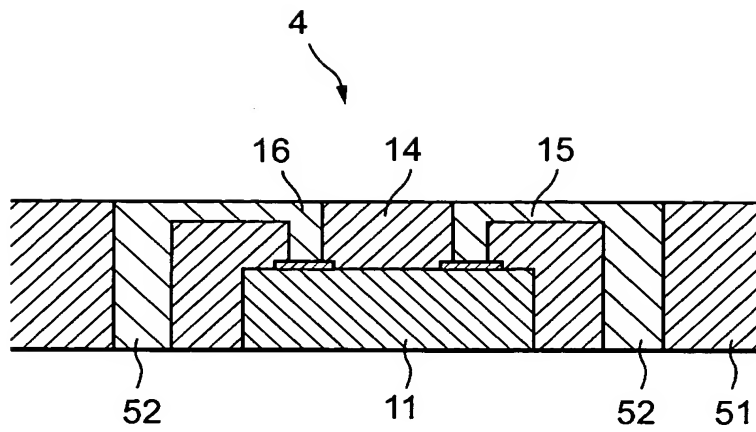


FIG. 8

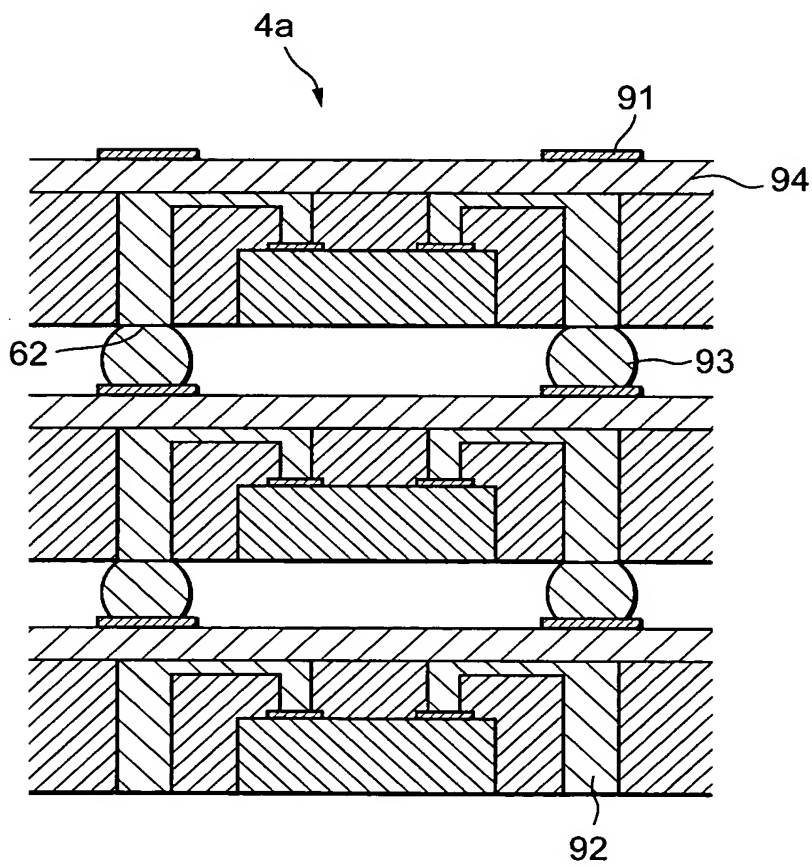


FIG. 9

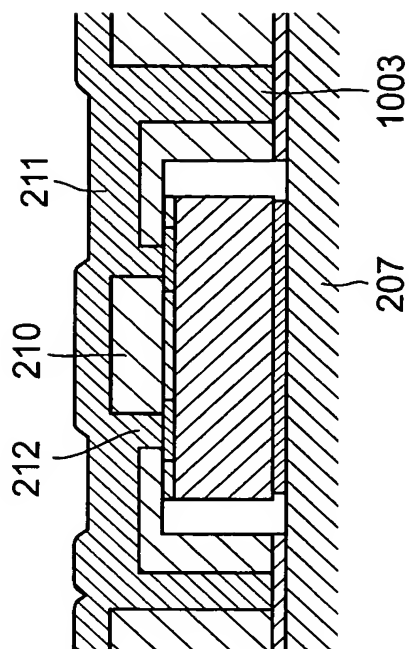


FIG. 10A

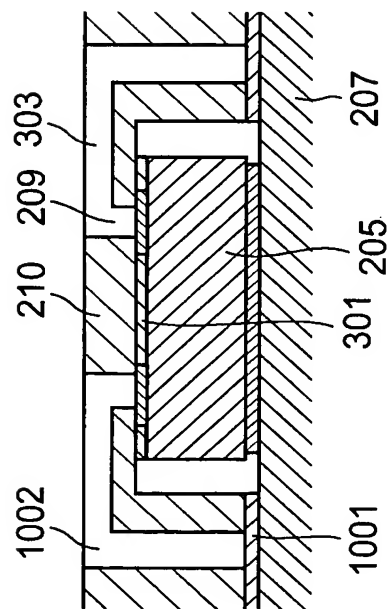


FIG. 10B

FIG. 10C

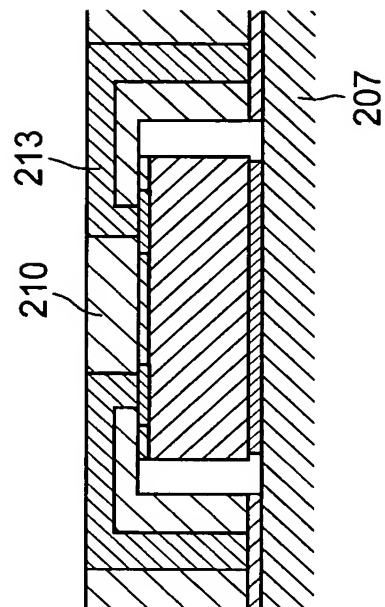


FIG. 10D

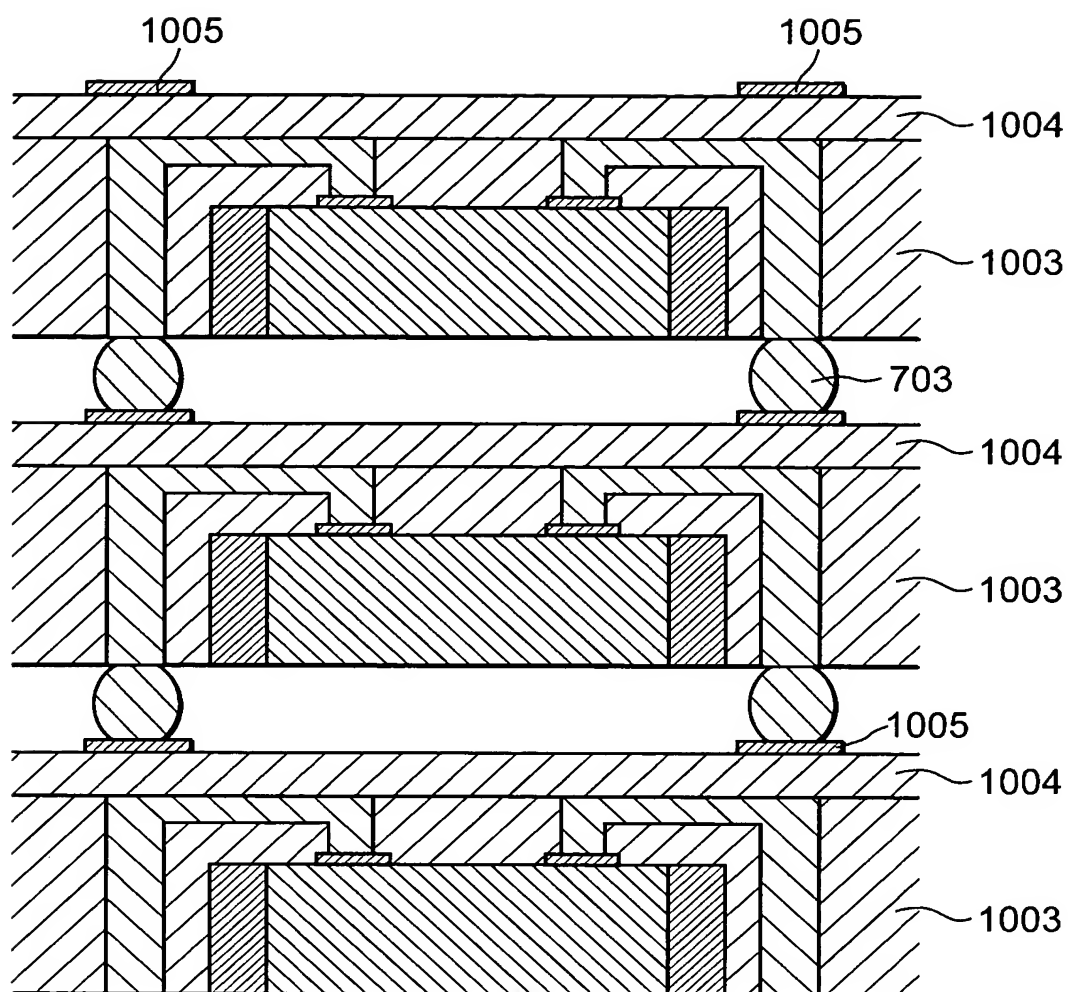


FIG. 10E